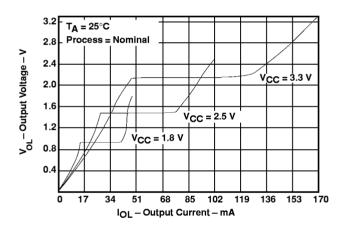
- EPIC™ (Enhanced-Performance Implanted CMOS) Submicron Process
- DOC™ (Dynamic Output Control) Circuit Dynamically Changes Output Impedance, Resulting in Noise Reduction Without Speed Degradation
- Dynamic Drive Capability Is Equivalent to Standard Outputs With I_{OH} and I_{OL} of ±24 mA at 2.5-V V_{CC}
- Overvoltage-Tolerant Inputs/Outputs Allow Mixed-Voltage-Mode Data Communications
- Package Options Include Plastic Small-Outline (D), Thin Very Small-Outline (DGV), and Thin Shrink Small-Outline (PW) Packages

description

A Dynamic Output Control (DOC) circuit is implemented, which, during the transition, initially lowers the output impedance to effectively drive the load and, subsequently, raises the impedance to reduce noise. Figure 1 shows typical V_{OL} vs I_{OL} and V_{OH} vs I_{OH} curves to illustrate the output impedance and drive capability of the circuit. At the beginning of the signal transition, the DOC circuit provides a maximum dynamic drive that is equivalent to a high-drive standard-output device. For more information, refer to the TI application reports, *AVC Logic Family Technology and Applications*, literature number SCEA006, and *Dynamic Output Control (DOC*TM) *Circuitry Technology and Applications*, literature number SCEA009.



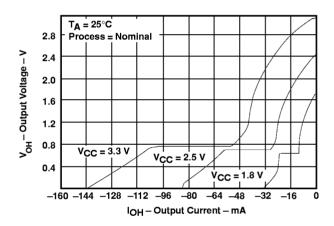


Figure 1. Output Voltage vs Output Current

This quadruple 2-input positive-NAND gate is operational at 1.2-V to 3.6-V V_{CC} , but designed specifically for 1.65-V to 3.6-V V_{CC} operation.

The SN74AVC00 performs the Boolean function $Y = \overline{A \cdot B}$ or $Y = \overline{A} + \overline{B}$ in positive logic.

The SN74AVC00 is characterized for operation from -40°C to 85°C.



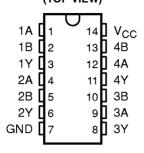
Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

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terminal assignments

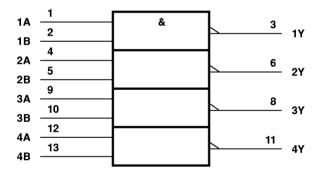
D, DGV, OR PW PACKAGE (TOP VIEW)



FUNCTION TABLE (each gate)

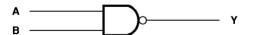
INP	JTS	OUTPUT
Α	В	Υ
Н	Н	L
L	Χ	Н
х	L	Н

logic symbol†



 $[\]ensuremath{^{\dagger}}$ This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram, each gate (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V _{CC}	
Input voltage range, V _I (see Note 1)	
Output voltage range, VO (see Notes 1 and 2)	—0.5 V to V _{CC} + 0.5 V
Input clamp current, $I_{ K }(V_{ } < 0)$	–50 mA
Output clamp current, I _{OK} (V _O < 0)	–50 mA
Continuous output current, IO	±50 mA
Continuous current through each V _{CC} or GND	±100 mA
Package thermal impedance, θ _{JA} (see Note 3):	D package 127°C/W
-	DGV package 182°C/W
	PW package 170°C/W
Storage temperature range, T _{sto}	—65°C to 150°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.
 - 2. The output positive-voltage rating may be exceeded up to 4.6 V maximum if the output current rating is observed.
 - 3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT	
V	Supply valtage	Operating	1.65	3.6	V	
vcc	Supply voltage	Data retention only	1.2		V	
		V _{CC} = 1.2 V	Vcc	'cc		
V	High lavel mank valence	V _{CC} = 1.65 V to 1.95 V	0.65 × V _{CC}		٧	
V_{IH}	High-level input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.7		V	
		$V_{CC} = 3 \text{ V to } 3.6 \text{ V}$	2			
		V _{CC} = 1.2 V		GND		
V	Lavy laval innut valtage	$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		0.35 × V _{CC}	V	
V _{IL}	Low-level input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		0.7	V	
		V _{CC} = 3 V to 3.6 V		0.8		
VΙ	Input voltage	•	0	3.6	V	
V-	Outros to valta a a	Active state	0	Vcc	V	
VO	Output voltage	3-state	0	3.6	V	
		V _{CC} = 1.65 V to 1.95 V		-4		
IOHS	Static high-level output current‡	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		-8	mA	
		$V_{CC} = 3 \text{ V to } 3.6 \text{ V}$		-12		
		V _{CC} = 1.65 V to 1.95 V		4		
lols	Static low-level output current‡	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		8	mA	
		V _{CC} = 3 V to 3.6 V		12		
Δt/Δν	Input transition rise or fall rate	V _{CC} = 1.65 V to 3.6 V		5	ns/V	
TA	Operating free-air temperature	•	-40	85	°C	

[‡] Dynamic drive capability is equivalent to standard outputs with I_{OH} and I_{OL} of ±24 mA at 2.5-V V_{CC}. See Figure 1 for V_{OL} vs I_{OL} and V_{OH} vs I_{OH} characteristics. Refer to the TI application reports, *AVC Logic Family Technology and Applications*, literature number **SCEA006**, and *Dynamic Output Control (DOC*[™]) *Circuitry Technology and Applications*, literature number **SCEA009**.

NOTE 4: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs. literature number SCBA004.



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electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TES	T CONDITIONS	v _{cc}	MIN	TYP	MAX	UNIT
	I _{OHS} = -100 μA		1.65 V to 3.6 V	V _{CC} -0.	2		
V	$I_{OHS} = -4 \text{ mA},$	V _{IH} = 1.07 V	1.65 V	1.2			v
VOH	$I_{OHS} = -8 \text{ mA},$	V _{IH} = 1.7 V	2.3 V	1.75			v
	$I_{OHS} = -12 \text{ mA},$	V _{IH} = 2 V	3 V	2.3			
	I _{OLS} = 100 μA		1.65 V to 3.6 V			0.2	15 V
Vai	$I_{OLS} = 4 \text{ mA},$	V _{IL} = 0.57 V	1.65 V			0.45	
V _{OL}	$I_{OLS} = 8 \text{ mA},$	$V_{IL} = 0.7 V$	2.3 V			0.55	
	$I_{OLS} = 12 \text{ mA},$	V _{IL} = 0.8 V	3 V			0.7	
1	$V_I = V_{CC}$ or GND		3.6 V			±2.5	μΑ
Icc	$V_I = V_{CC}$ or GND,	I _O = 0	3.6 V			40	μΑ
C:	V. Von er GND		2.5 V				ρF
C _i	$V_I = V_{CC}$ or GND		3.3 V				þг

[†] Typical values are measured at T_A = 25°C.

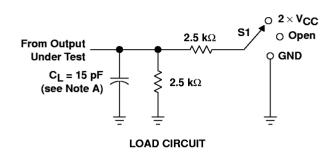
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 2 through 6)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} =	1.2 V	V _{CC} =		V _{CC} = ± 0.1		V _{CC} =		V _{CC} = ± 0.3		UNIT
	(1141-01)	(0011-01)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd}	A or B	Υ				_		·					ns

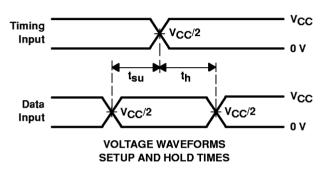
operating characteristics, $T_A = 25^{\circ}C$

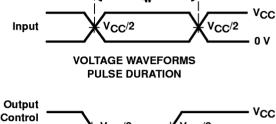
ſ	PARAMETER		TEST CONDITIONS		V _{CC} = 1.8 V V _{CC} = 2.5 V V _{CC}		$V_{CC} = 3.3 \text{ V}$	UNIT
L					TYP	TYP	TYP	ONT
	C _{pd}	Power dissipation capacitance per gate	C _L = 0,	f = 10 MHz				pF

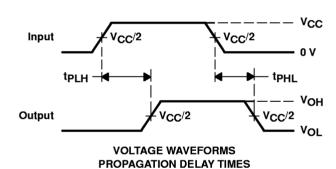
PARAMETER MEASUREMENT INFORMATION V_{CC} = 1.2 V

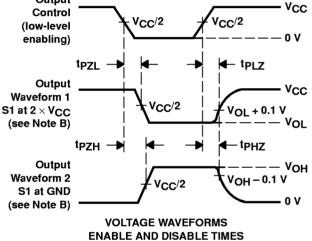


TEST	S1
t _{pd}	Open
t _{PLZ} /t _{PZL}	2×V _{CC}
t _{PHZ} /t _{PZH}	GND









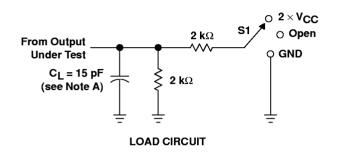
NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_f \leq$ 2 ns, $t_f \leq$ 2 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpl 7 and tpH7 are the same as t_{dis}.
- F. tpzL and tpzH are the same as ten.
- G. tplH and tpHL are the same as tod.

Figure 2. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION $V_{CC} = 1.5 \text{ V} \pm 0.1 \text{ V}$

Input



TEST	S1
t _{pd}	Open
t _{PLZ} /t _{PZL}	2×V _{CC}
tPHZ/tPZH	GND

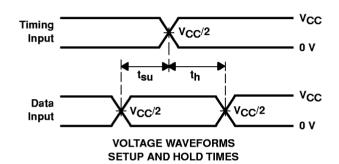
V_{CC}/2

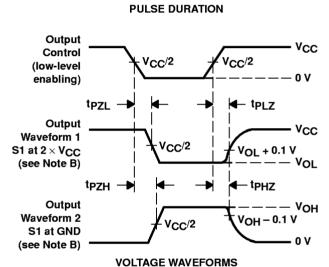
VOLTAGE WAVEFORMS

Vcc

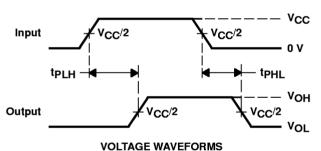
nν

V_{CC}/2





ENABLE AND DISABLE TIMES



PROPAGATION DELAY TIMES

- NOTES: A. C_L includes probe and jig capacitance.

 B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control.

 Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_f \leq$ 2 ns, $t_f \leq$ 2 ns.
 - D. The outputs are measured one at a time with one transition per measurement.
 - E. tpLz and tpHz are the same as tdis-
 - F. tpzL and tpzH are the same as ten-
 - G. tpLH and tpHL are the same as tod.

Figure 3. Load Circuit and Voltage Waveforms



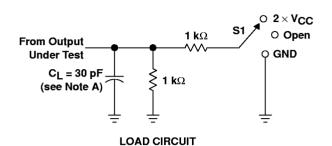
V_{CC}

0 V

V_{CC}/2

PARAMETER MEASUREMENT INFORMATION $V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V}$

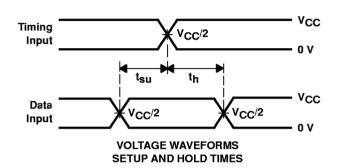
Input

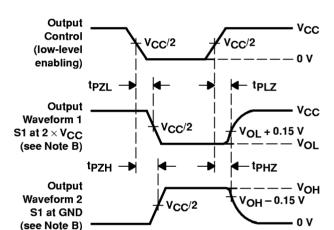


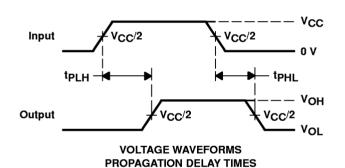
TEST	S1
tpd	Open
tpLZ/tpZL	2×V _{CC}
tPHZ/tPZH	GND

V_{CC}/2

VOLTAGE WAVEFORMS
PULSE DURATION







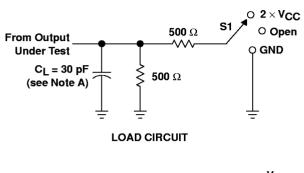
VOLTAGE WAVEFORMS ENABLE AND DISABLE TIMES

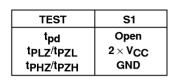
NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \ \Omega$, $t_f \leq 2 \ ns$, $t_f \leq 2 \ ns$.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLZ and tpHZ are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tplH and tpHL are the same as tod.

Figure 4. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION $V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$





V_{CC}/2

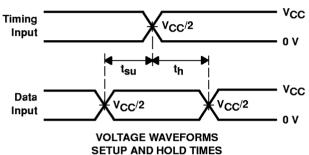
VOLTAGE WAVEFORMS

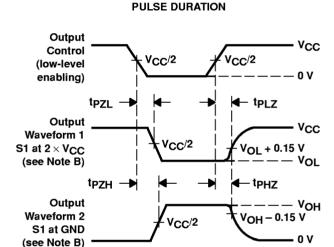
Input

V_{CC}

0 V

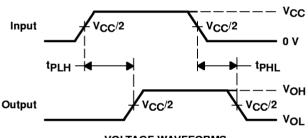
V_{CC}/2





VOLTAGE WAVEFORMS

ENABLE AND DISABLE TIMES



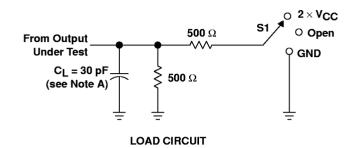
VOLTAGE WAVEFORMS PROPAGATION DELAY TIMES

NOTES: A. C_L includes probe and jig capacitance.

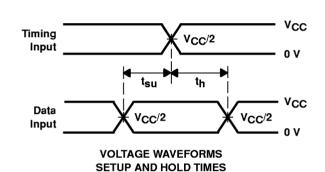
- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \ \Omega$, $t_f \leq$ 2 ns. $t_f \leq$ 2 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLZ and tpHZ are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tplH and tpHL are the same as tod.

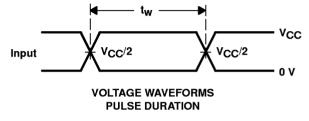
Figure 5. Load Circuit and Voltage Waveforms

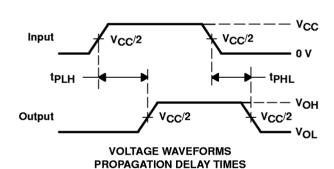
PARAMETER MEASUREMENT INFORMATION $V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$

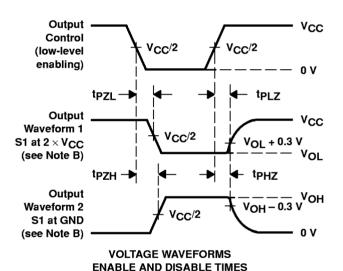


TEST	S1
t _{pd}	Open
tPLZ/tPZL	$2 \times V_{CC}$
^t PHZ ^{/t} PZH	GND









NOTES: A. C_I includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \ \Omega$, $t_f \leq$ 2 ns. $t_f \leq$ 2 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpl 7 and tpH7 are the same as tdis.
- F. tp_{ZL} and tp_{ZH} are the same as t_{en} .
- G. tpLH and tpHL are the same as tpd.

Figure 6. Load Circuit and Voltage Waveforms

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